

Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.8)	V_{pp}	4.5	kV
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($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V R_L=33$	- -	MAX.	20	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	$V_D=V_{DRM} T_j=150$ $R_L=3.3K$	- -	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	-	MAX.	25	mA
				55	
I_H	$I_T=500mA$		MAX.	25	mA
dV/dt	$V_D=400V$ Gate Open $T_j=150$		MIN.	500	V/ μs
$(dI/dt)_c$	$(dV/dt)_c=20V/\mu s, T_j=150$		MIN.	3	A/ms
t_{on}	$I_G=40mA I_A=200mA I_R=20mA$ $T_j=25$		TYP.	3	μs
t_{off}				60	

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=17A t_p=380\mu s$	$T_j=25$	1.4	V
V_{TO}	Threshold voltage	$T_j=150$	0.75	V
R_D	Dynamic resistance	$T_j=150$	37	m
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25$	5	μA
I_{RRM}		$T_j=150$	1.5	mA

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	1.3	W
$R_{th(j-a)}$	junction to ambient	3	W

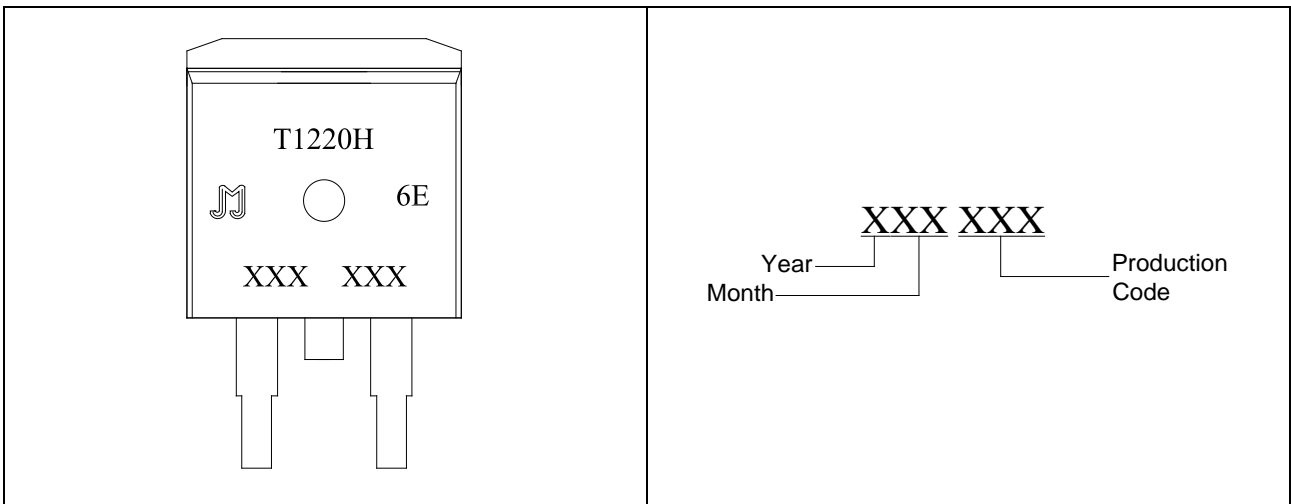
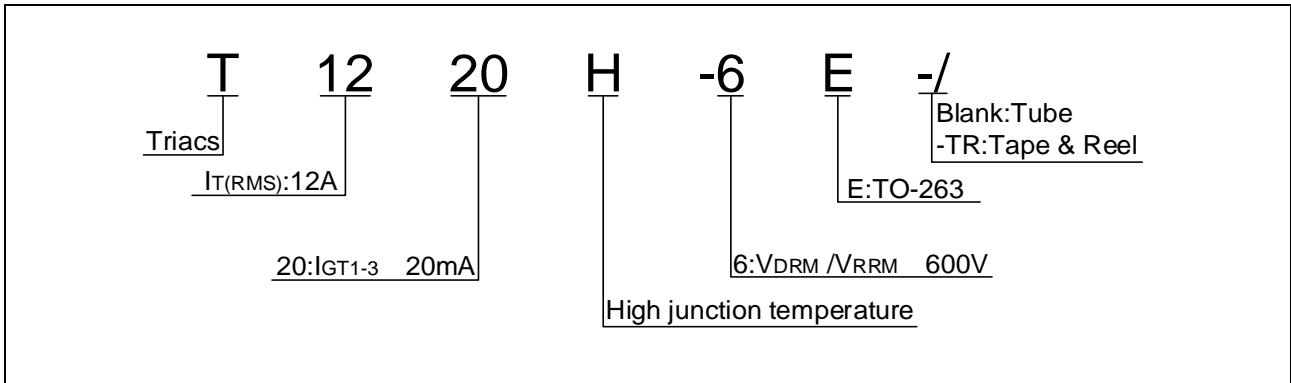


FIG.1 Maximum power dissipation versus RMS on-state current

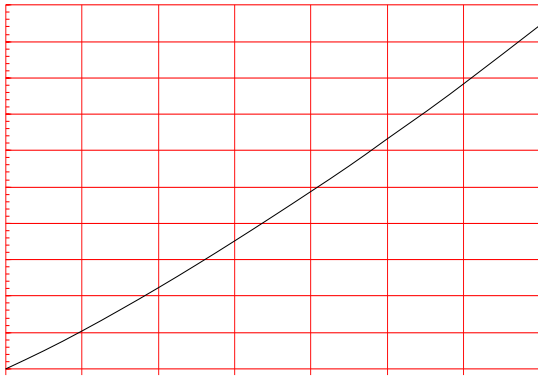


FIG.2: RMS on-state current versus case temperature

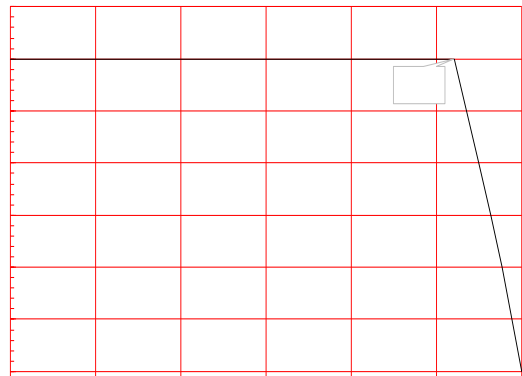


FIG.3: RMS on-state current versus ambient temperature (printed circuit board FR4,copper thickness:35μm)(full cycle)

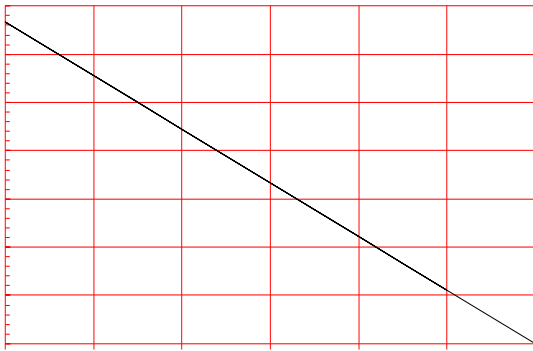
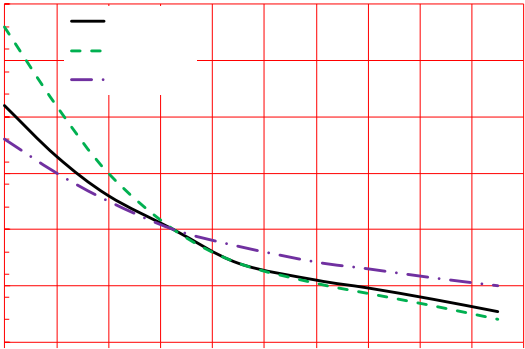


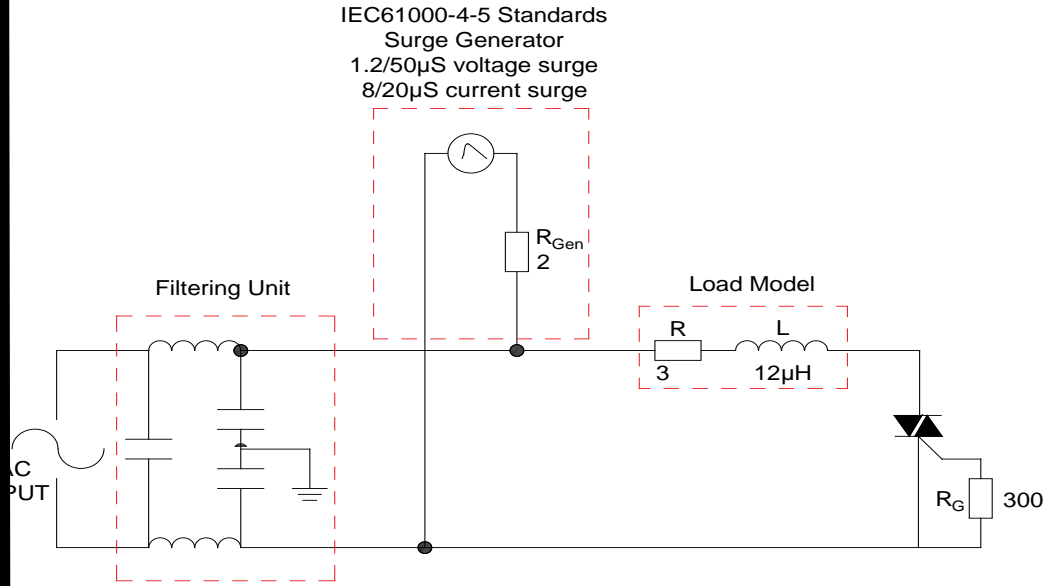
FIG.4: Surge peak on-state current versus number of cycles



FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature




6.8 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		- -			
T1220H-6E	600	20	TO-263	50	Tube
T1220H-6E-TR				800	Tape & Reel

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